

INTRODUCE:

HVGT high voltage silicon rectifier assembly is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Fast recovery.
2. GPP chips.
3. High current . low forward voltage
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Accelerator power supply.
2. High voltage test equipment circuit .
3. General purpose high voltage rectifier.
4. Environmental desulfurization system.

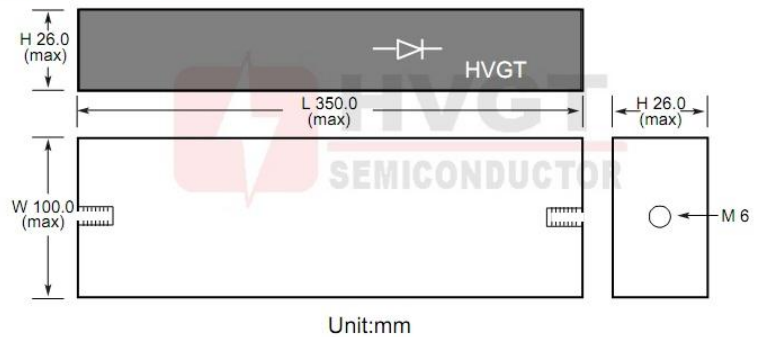
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: screw holes.
3. Net weight: 1510 grams (approx).

SHAPE DISPLAY:

SIZE: (Unit:mm)
HVGT NAME: HVC-351026
HVC-301026 Series

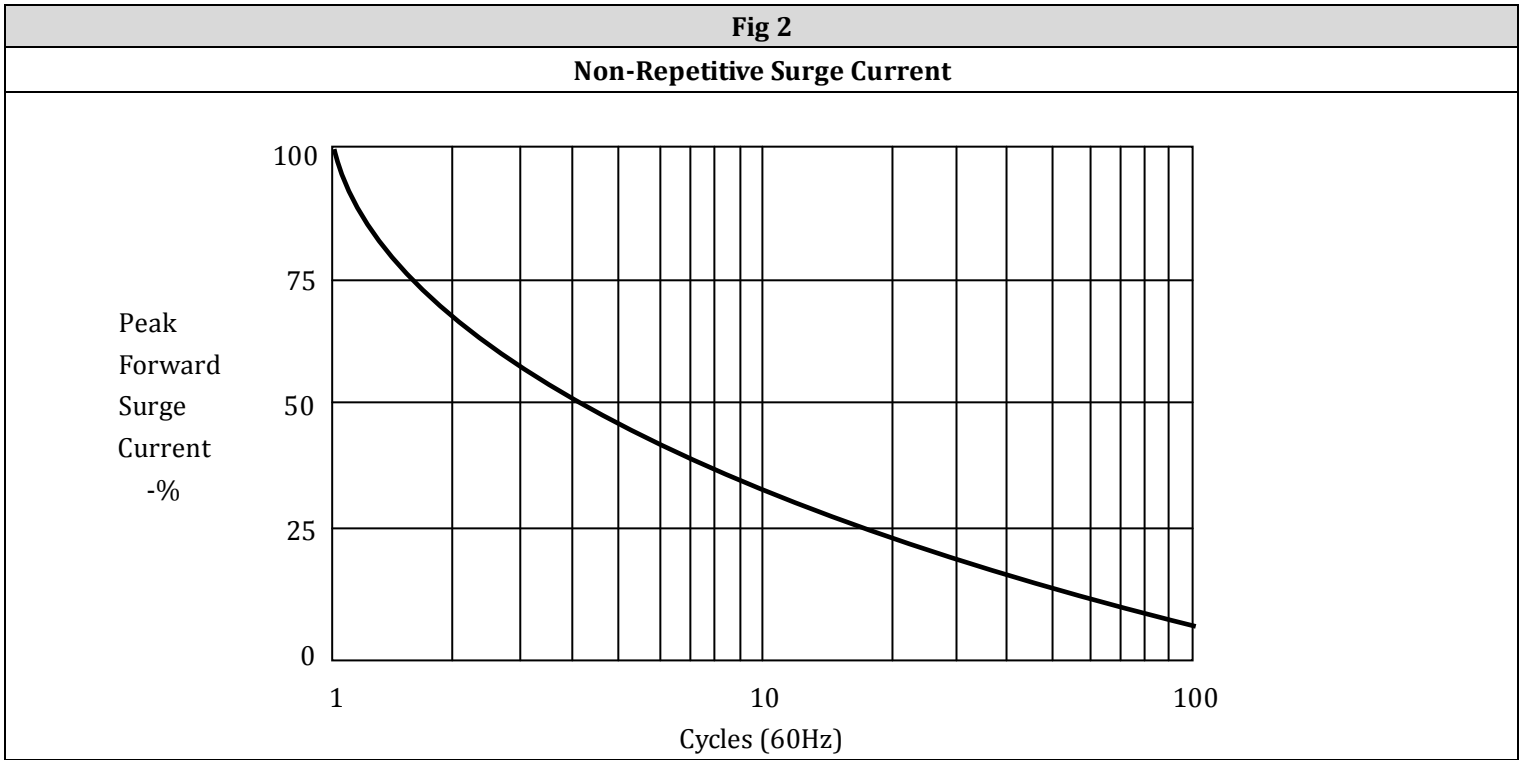
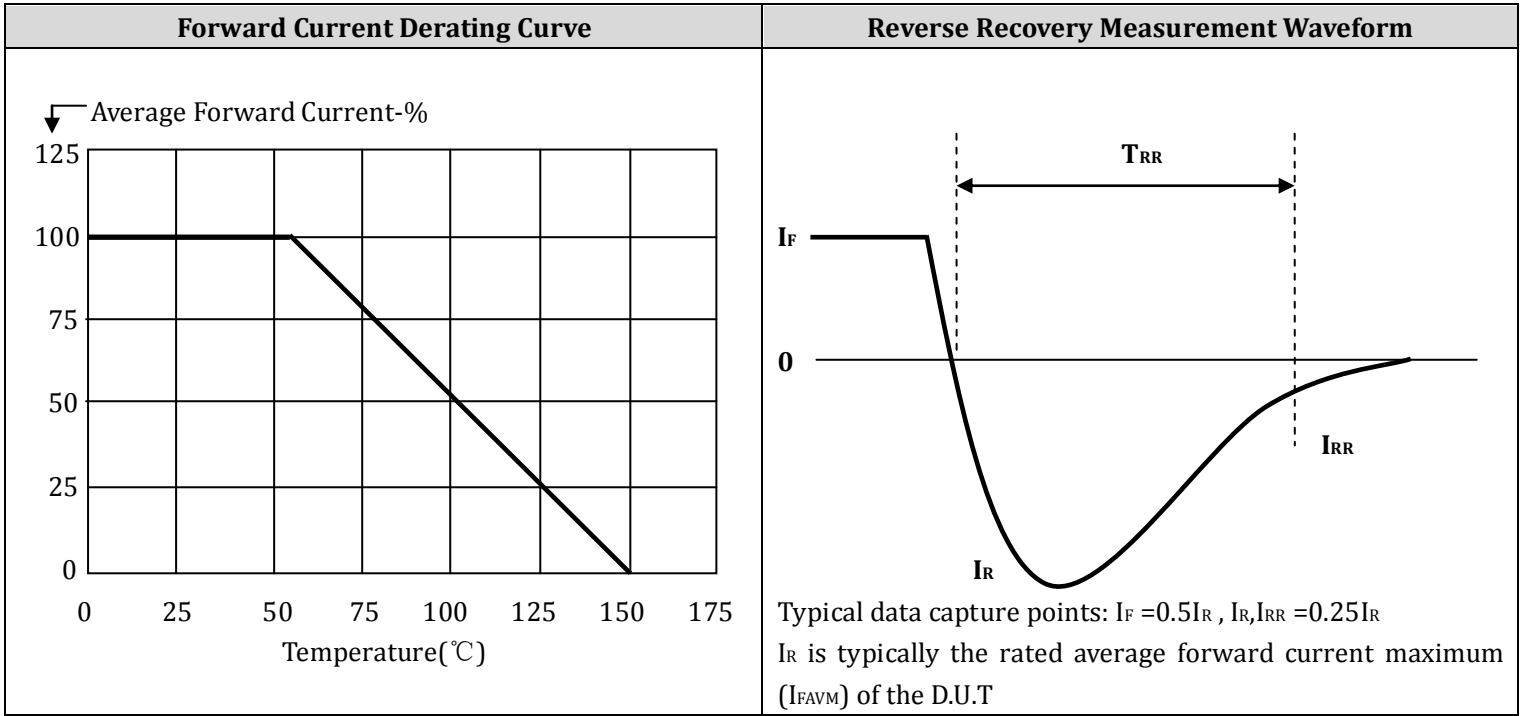
Screw Holes M6


MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	200	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$	240	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=55^{\circ}C$	3.0	A
		$T_{OIL}=55^{\circ}C$	4.0	A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 60Hz Half-Sine Wave; 8.3mS	60	A
Junction Temperature	T_J		150	$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+150	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+175	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	300	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	5.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	50	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	100	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--	pF



Marking	Type	Code	Cathode Mark
	YGL30A201G	YGL30A201G HVGT	